

Francesco La Via

List of Publications by Year in Descending Order

Source: <https://exaly.com/author-pdf/5670515/francesco-la-via-publications-by-year.pdf>

Version: 2024-04-27

This document has been generated based on the publications and citations recorded by exaly.com. For the latest version of this publication list, visit the link given above.

The third column is the impact factor (IF) of the journal, and the fourth column is the number of citations of the article.

371
papers

3,786
citations

26
h-index

44
g-index

391
ext. papers

4,147
ext. citations

1.9
avg, IF

5.07
L-index

#	Paper	IF	Citations
371	The development of a fully MRI-compatible silicon carbide neural interface 2022 , 161-195		
370	Status and Prospects of Cubic Silicon Carbide Power Electronics Device Technology. <i>Materials</i> , 2021 , 14,	3.5	2
369	Status of 3 C - SiC Growth and Device Technology 2021 , 93-136		
368	Initial investigations into the MOS interface of freestanding 3C-SiC layers for device applications. <i>Semiconductor Science and Technology</i> , 2021 , 36, 055006	1.8	0
367	Growth of thick [111]-oriented 3C-SiC films on T-shaped Si micropillars. <i>Materials and Design</i> , 2021 , 109883		2
366	Overgrowth of Protrusion Defects during Sublimation Growth of Cubic Silicon Carbide Using Free-Standing Cubic Silicon Carbide Substrates. <i>Crystal Growth and Design</i> , 2021 , 21, 4046-4054	3.5	3
365	A study on free-standing 3C-SiC bipolar power diodes. <i>Applied Physics Letters</i> , 2021 , 118, 242101	3.4	1
364	Silicon Carbide and MRI: Towards Developing a MRI Safe Neural Interface. <i>Micromachines</i> , 2021 , 12,	3.3	7
363	Mechanism of stacking fault annihilation in 3C-SiC epitaxially grown on Si(001) by molecular dynamics simulations. <i>CrystEngComm</i> , 2021 , 23, 1566-1571	3.3	3
362	Epitaxial Growth and Characterization of 4H-SiC for Neutron Detection Applications. <i>Materials</i> , 2021 , 14,	3.5	4
361	Extended defects in 3C-SiC: Stacking faults, threading partial dislocations, and inverted domain boundaries. <i>Acta Materialia</i> , 2021 , 213, 116915	8.4	11
360	Effect of Nitrogen and Aluminum Doping on 3C-SiC Heteroepitaxial Layers Grown on 4° Off-Axis Si (100). <i>Materials</i> , 2021 , 14,	3.5	3
359	Measurement of Residual Stress and Young's Modulus on Micromachined Monocrystalline 3C-SiC Layers Grown on and Silicon. <i>Micromachines</i> , 2021 , 12,	3.3	1
358	New Approaches and Understandings in the Growth of Cubic Silicon Carbide. <i>Materials</i> , 2021 , 14,	3.5	6
357	Prospects of Bulk Growth of 3C-SiC Using Sublimation Growth. <i>Materials Science Forum</i> , 2020 , 1004, 113-119	1.1	4
356	4H-SiC MOSFET Source and Body Laser Annealing Process. <i>Materials Science Forum</i> , 2020 , 1004, 705-711	0.4	1
355	Generation and Termination of Stacking Faults by Inverted Domain Boundaries in 3C-SiC. <i>Crystal Growth and Design</i> , 2020 , 20, 3104-3111	3.5	9

354	Silicon Carbide devices for radiation detection and measurements. <i>Journal of Physics: Conference Series</i> , 2020 , 1561, 012013	0.3	0
353	Impact of Stacking Faults and Domain Boundaries on the Electronic Transport in Cubic Silicon Carbide Probed by Conductive Atomic Force Microscopy. <i>Advanced Electronic Materials</i> , 2020 , 6, 1901171	6.4	16
352	Genesis and evolution of extended defects: The role of evolving interface instabilities in cubic SiC. <i>Applied Physics Reviews</i> , 2020 , 7, 021402	17.3	22
351	Characterization of 4H- and 6H-Like Stacking Faults in Cross Section of 3C-SiC Epitaxial Layer by Room-Temperature Photoluminescence and Raman Analysis. <i>Materials</i> , 2020 , 13,	3.5	6
350	Recent results on heavy-ion induced reactions of interest for neutrinoless double beta decay at INFN-LNS. <i>Journal of Physics: Conference Series</i> , 2020 , 1643, 012074	0.3	0
349	On the origin of the premature breakdown of thermal oxide on 3C-SiC probed by electrical scanning probe microscopy. <i>Applied Surface Science</i> , 2020 , 526, 146656	6.7	4
348	Ni/4H-SiC interaction and silicide formation under excimer laser annealing for ohmic contact. <i>Materialia</i> , 2020 , 9, 100528	3.2	10
347	Recent results on heavy-ion direct reactions of interest for $0\nu\beta\beta$ decay at INFN - LNS. <i>Journal of Physics: Conference Series</i> , 2020 , 1610, 012004	0.3	
346	The NUMEN Heavy Ion Multidetector for a Complementary Approach to the Neutrinoless Double Beta Decay. <i>Universe</i> , 2020 , 6, 129	2.5	9
345	3C-SiC Bulk Growth: Effect of Growth Rate and Doping on Defects and Stress. <i>Materials Science Forum</i> , 2020 , 1004, 120-125	0.4	5
344	Silicon Carbide characterization at the n_TOF spallation source with quasi-monoenergetic fast neutrons. <i>Nuclear Instruments and Methods in Physics Research, Section A: Accelerators, Spectrometers, Detectors and Associated Equipment</i> , 2020 , 983, 164578	1.2	1
343	High Quality 4H-SiC Epitaxial Layer by Tuning CVD Process. <i>Materials Science Forum</i> , 2019 , 963, 91-96	0.4	2
342	New thick silicon carbide detectors: Response to 14 MeV neutrons and comparison with single-crystal diamonds. <i>Nuclear Instruments and Methods in Physics Research, Section A: Accelerators, Spectrometers, Detectors and Associated Equipment</i> , 2019 , 946, 162637	1.2	8
341	Growth and Coalescence of 3C-SiC on Si(111) Micro-Pillars by a Phase-Field Approach. <i>Materials</i> , 2019 , 12,	3.5	5
340	Ohmic contacts on n-type and p-type cubic silicon carbide (3C-SiC) grown on silicon. <i>Materials Science in Semiconductor Processing</i> , 2019 , 93, 295-298	4.3	7
339	Nuclear fragment identification with E-E telescopes exploiting silicon carbide detectors. <i>Nuclear Instruments and Methods in Physics Research, Section A: Accelerators, Spectrometers, Detectors and Associated Equipment</i> , 2019 , 925, 60-69	1.2	7
338	3C-SiC grown on Si by using a Si _{1-x} Gex buffer layer. <i>Journal of Crystal Growth</i> , 2019 , 519, 1-6	1.6	8
337	Biocompatibility between Silicon or Silicon Carbide surface and Neural Stem Cells. <i>Scientific Reports</i> , 2019 , 9, 11540	4.9	16

336	High Resolution Investigation of Stacking Fault Density by HRXRD and STEM. <i>Materials Science Forum</i> , 2019 , 963, 346-349	0.4	4
335	Thermal Annealing of High Dose P Implantation in 4H-SiC. <i>Materials Science Forum</i> , 2019 , 963, 399-402	0.4	5
334	Growth of Large-Area, Stress-Free, and Bulk-Like 3C-SiC (100) Using 3C-SiC-on-Si in Vapor Phase Growth. <i>Materials</i> , 2019 , 12,	3.5	7
333	Limitations during Vapor Phase Growth of Bulk (100) 3C-SiC Using 3C-SiC-on-SiC Seeding Stacks. <i>Materials</i> , 2019 , 12,	3.5	5
332	Fabrication of a Monolithic Implantable Neural Interface from Cubic Silicon Carbide. <i>Micromachines</i> , 2019 , 10,	3.3	17
331	Recent results on Heavy-Ion induced reactions of interest for $0\nu\beta\beta$ decay. <i>Journal of Physics: Conference Series</i> , 2019 , 1308, 012002	0.3	
330	Laser Annealing of P and Al Implanted 4H-SiC Epitaxial Layers. <i>Materials</i> , 2019 , 12,	3.5	7
329	Temperature Investigation on 3C-SiC Homo-Epitaxy on Four-Inch Wafers. <i>Materials</i> , 2019 , 12,	3.5	11
328	The NUMEN project @ LNS: Status and perspectives 2019 ,		1
327	Recent results on heavy-ion induced reactions of interest for neutrinoless double beta decay at INFN-LNS. <i>EPJ Web of Conferences</i> , 2019 , 223, 01009	0.3	
326	Fabrication and Characterization of Ohmic Contacts to 3C-SiC Layers Grown on Silicon. <i>Materials Science Forum</i> , 2019 , 963, 485-489	0.4	2
325	Electrical Properties of Thermal Oxide on 3C-SiC Layers Grown on Silicon. <i>Materials Science Forum</i> , 2019 , 963, 479-482	0.4	2
324	Electrical Characterisation of Thick 3C-SiC Layers Grown on Off-Axis 4H-SiC Substrates. <i>Materials Science Forum</i> , 2019 , 963, 353-356	0.4	
323	3C-SiC Growth on Inverted Silicon Pyramids Patterned Substrate. <i>Materials</i> , 2019 , 12,	3.5	8
322	Vapor Growth of 3C-SiC Using the Transition Layer of 3C-SiC on Si CVD Templates. <i>Materials Science Forum</i> , 2019 , 963, 149-152	0.4	2
321	Simulation of the Growth Kinetics in Group IV Compound Semiconductors. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2019 , 216, 1800597	1.6	3
320	X-ray diffraction on stacking faults in 3C-SiC epitaxial microcrystals grown on patterned Si(0 0 1) wafers. <i>Journal of Crystal Growth</i> , 2019 , 507, 70-76	1.6	4
319	From thin film to bulk 3C-SiC growth: Understanding the mechanism of defects reduction. <i>Materials Science in Semiconductor Processing</i> , 2018 , 78, 57-68	4.3	72

318	Stress Relaxation Mechanism after Thinning Process on 4H-SiC Substrate. <i>Materials Science Forum</i> , 2018 , 924, 535-538	0.4	3
317	Growth of 4H-SiC Epitaxial Layer through Optimization of Buffer Layer. <i>Materials Science Forum</i> , 2018 , 924, 84-87	0.4	5
316	Double Step Annealing for the Recovering of Ion Implantation Defectiveness in 4H-SiC DIMOSFET. <i>Materials Science Forum</i> , 2018 , 924, 357-360	0.4	
315	Silicon Carbide detectors for nuclear physics experiments at high beam luminosity. <i>Journal of Physics: Conference Series</i> , 2018 , 1056, 012032	0.3	3
314	The NUMEN project: NUClear Matrix Elements for Neutrinoless double beta decay. <i>European Physical Journal A</i> , 2018 , 54, 1	2.5	92
313	Protrusions reduction in 3C-SiC thin film on Si. <i>Journal of Crystal Growth</i> , 2018 , 498, 248-257	1.6	17
312	3C-SiC Hetero-Epitaxially Grown on Silicon Compliance Substrates and New 3C-SiC Substrates for Sustainable Wide-Band-Gap Power Devices (CHALLENGE). <i>Materials Science Forum</i> , 2018 , 924, 913-918	0.4	10
311	Measuring nuclear reaction cross sections to extract information on neutrinoless double beta decay. <i>Journal of Physics: Conference Series</i> , 2018 , 966, 012021	0.3	0
310	SiCILIA-Silicon Carbide Detectors for Intense Luminosity Investigations and Applications. <i>Sensors</i> , 2018 , 18,	3.8	25
309	Solving the critical thermal bowing in 3C-SiC/Si(111) by a tilting Si pillar architecture. <i>Journal of Applied Physics</i> , 2018 , 123, 185703	2.5	5
308	Stacking Faults Defects on 3C-SiC Homo-Epitaxial Films. <i>Materials Science Forum</i> , 2018 , 924, 124-127	0.4	4
307	Formation, Morphology, and Optical Properties of Electroless Deposited Gold Nanoparticles on 3C-SiC. <i>Journal of Physical Chemistry C</i> , 2017 , 121, 4304-4311	3.8	9
306	Electrical properties of extended defects in 4H-SiC investigated by photoinduced current measurements. <i>Applied Physics Express</i> , 2017 , 10, 036601	2.4	6
305	3C-SiC Bulk Sublimation Growth on CVD Hetero-Epitaxial Seeding Layers. <i>Materials Science Forum</i> , 2017 , 897, 15-18	0.4	1
304	Carbonization and transition layer effects on 3C-SiC film residual stress. <i>Journal of Crystal Growth</i> , 2017 , 473, 11-19	1.6	17
303	Growing bulk-like 3C-SiC from seeding material produced by CVD. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2017 , 214, 1600429	1.6	2
302	Sublimation growth of bulk 3C-SiC using 3C-SiC-on-Si (1 0 0) seeding layers. <i>Journal of Crystal Growth</i> , 2017 , 478, 159-162	1.6	15
301	Photo-electrochemical water splitting in silicon based photocathodes enhanced by plasmonic/catalytic nanostructures. <i>Materials Science and Engineering B: Solid-State Materials for Advanced Technology</i> , 2017 , 225, 128-133	3.1	9

300	4H-SiC Defects Evolution by Thermal Processes. <i>Materials Science Forum</i> , 2017 , 897, 181-184	0.4	4
299	Detection of Crystallographic Defects in 3C-SiC by Micro-Raman and Micro-PL Analysis. <i>Materials Science Forum</i> , 2017 , 897, 303-306	0.4	6
298	The NUMEN project @ LNS: Status and perspectives 2017 ,		1
297	NURE: An ERC project to study nuclear reactions for neutrinoless double beta decay 2017 ,		3
296	Characterization of protrusions and stacking faults in 3C-SiC grown by sublimation epitaxy using 3C-SiC-on-Si seeding layers. <i>Advanced Materials Proceedings</i> , 2017 , 2, 774-778	1	2
295	Photocatalytical activity of amorphous hydrogenated TiO ₂ obtained by pulsed laser ablation in liquid. <i>Materials Science in Semiconductor Processing</i> , 2016 , 42, 28-31	4.3	19
294	Hydrogen Flux Influence on Homo-Epitaxial 4H-SiC Doping Concentration Profile for High Power Application. <i>Materials Science Forum</i> , 2016 , 858, 197-200	0.4	1
293	The nuclear matrix elements of $0\nu\beta\beta$ decay and the NUMEN project at INFN-LNS. <i>Journal of Physics: Conference Series</i> , 2016 , 730, 012006	0.3	1
292	Ion Implantation Defects in 4H-SiC DIMOSFET. <i>Materials Science Forum</i> , 2016 , 858, 418-421	0.4	11
291	High growth rate 3C-SiC growth: from hetero-epitaxy to homo-epitaxy. <i>MRS Advances</i> , 2016 , 1, 3643-3647	0.7	2
290	Optimization of Ion Implantation processes for 4H-SiC DIMOSFET. <i>MRS Advances</i> , 2016 , 1, 3673-3678	0.7	2
289	Silicon carbide detectors study for NUMEN project. <i>EPJ Web of Conferences</i> , 2016 , 117, 10006	0.3	25
288	Electrical Properties of Defects in 4H-SiC Investigated by Photo-Induced-Currents Measurements. <i>Materials Science Forum</i> , 2016 , 858, 380-383	0.4	1
287	Structural and electronic transitions in Ge ₂ Sb ₂ Te ₅ induced by ion irradiation damage. <i>Physical Review B</i> , 2016 , 94,	3.3	24
286	Physical Vapor Growth of Double Position Boundary Free, Quasi-Bulk 3C-SiC on High Quality 3C-SiC on Si CVD Templates. <i>Materials Science Forum</i> , 2016 , 858, 89-92	0.4	6
285	Stacking Fault Analysis of Epitaxial 3C-SiC on Si(001) Ridges. <i>Materials Science Forum</i> , 2016 , 858, 147-150	0.4	10
284	3C-SiC Epitaxy on Deeply Patterned Si(111) Substrates. <i>Materials Science Forum</i> , 2016 , 858, 151-154	0.4	9
283	Voids-Free 3C-SiC/Si Interface for High Quality Epitaxial Layer. <i>Materials Science Forum</i> , 2016 , 858, 159-162		2

282	Correlations between Crystal Quality and Electrical Properties by Means of Simultaneous Photoluminescence and Photocurrent Analysis. <i>Materials Science Forum</i> , 2015 , 821-823, 257-260	0.4	
281	3C-SiC Polycrystalline Films on Si for Photovoltaic Applications. <i>Materials Science Forum</i> , 2015 , 821-823, 189-192	0.4	3
280	Interface state density evaluation of high quality hetero-epitaxial 3C-SiC(001) for high-power MOSFET applications. <i>Materials Science and Engineering B: Solid-State Materials for Advanced Technology</i> , 2015 , 198, 14-19	3.1	14
279	Epitaxial Growth on 150 mm 2 μ off Wafers. <i>Materials Science Forum</i> , 2015 , 821-823, 157-160	0.4	1
278	Defect Reduction in Epitaxial 3C-SiC on Si(001) and Si(111) by Deep Substrate Patterning. <i>Materials Science Forum</i> , 2015 , 821-823, 193-196	0.4	11
277	Monte Carlo Study of the early Growth Stages of 3C-SiC on Misoriented <11-20> and <1-100>; 6H-SiC Substrates: Role of Step-Island Interaction. <i>Materials Science Forum</i> , 2015 , 821-823, 201-204	0.4	1
276	4H-SiC Defects Analysis by Micro Raman Spectroscopy. <i>Materials Science Forum</i> , 2015 , 821-823, 335-338	0.4	1
275	Electrical Properties Evaluation on High Quality Hetero-Epitaxial 3C-SiC(001) for MOSFET Applications. <i>Materials Science Forum</i> , 2015 , 821-823, 773-776	0.4	3
274	Hetero-Epitaxial Single Crystal 3C-SiC Opto-Mechanical Pressure Sensor. <i>Materials Science Forum</i> , 2015 , 821-823, 902-905	0.4	1
273	Laser plasma monitored by silicon carbide detectors. <i>Radiation Effects and Defects in Solids</i> , 2015 , 170, 303-324	0.9	3
272	Study of the role of particle-particle dipole interaction in dielectrophoretic devices for biomarkers identification. <i>Lecture Notes in Electrical Engineering</i> , 2015 , 9-12	0.2	3
271	Micro-Raman Characterization of 4H-SiC Stacking Faults. <i>Materials Science Forum</i> , 2014 , 778-780, 378-380	0.4	6
270	Electrically Trimmable Phase Change Ge ₂ Sb ₂ Te ₅ Resistors With Tunable Temperature Coefficient of Resistance. <i>IEEE Transactions on Electron Devices</i> , 2014 , 61, 2879-2885	2.9	3
269	Theoretical and experimental study of the role of cell-cell dipole interaction in dielectrophoretic devices: application to polynomial electrodes. <i>BioMedical Engineering OnLine</i> , 2014 , 13, 71	4.1	14
268	Evaluation of 3C-SiC/Si residual stress and curvatures along different wafer direction. <i>Materials Letters</i> , 2014 , 118, 130-133	3.3	8
267	MeV ion beams generated by intense pulsed laser monitored by Silicon Carbide detectors. <i>Journal of Physics: Conference Series</i> , 2014 , 508, 012009	0.3	2
266	Strain Evaluation and Fracture Properties of Hetero-Epitaxial Single Crystal 3C-SiC Squared Membrane. <i>Materials Science Forum</i> , 2014 , 806, 11-14	0.4	
265	Monte Carlo study of the early growth stages of 3C-SiC on misoriented and 6H-SiC substrates: role of step-island interaction. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2014 , 11, 1606-1610		

264	Mechanisms of growth and defect properties of epitaxial SiC. <i>Applied Physics Reviews</i> , 2014 , 1, 031301	17.3	56
263	A novel micro-Raman technique to detect and characterize 4H-SiC stacking faults. <i>Journal of Applied Physics</i> , 2014 , 116, 163506	2.5	8
262	4H-SiC Epitaxial Layer Grown on 150 mm Automatic Horizontal Hot Wall Reactor PE106. <i>Materials Science Forum</i> , 2014 , 778-780, 121-124	0.4	7
261	Effects of the Growth Rate on the Quality of 4H Silicon Carbide Films for MOSFET Applications. <i>Materials Science Forum</i> , 2014 , 778-780, 95-98	0.4	1
260	Curvature Evaluation of Si/3C-SiC/Si Hetero-Structure Grown by Chemical Vapor Deposition. <i>Materials Science Forum</i> , 2014 , 778-780, 255-258	0.4	
259	(Invited) Three-Dimensional Epitaxial Si _{1-x} Ge _x , Ge and SiC Crystals on Deeply Patterned Si Substrates. <i>ECS Transactions</i> , 2014 , 64, 631-648	1	12
258	Analysis on 3C-SiC Layer Grown on Pseudomorphic-Si/Si _{1-x} Ge _x /Si(001) Heterostructures. <i>Materials Science Forum</i> , 2014 , 806, 21-25	0.4	6
257	Monte Carlo Study of the Early Growth Stages of 3C-SiC on Misoriented and 6H-SiC Substrates. <i>Materials Science Forum</i> , 2014 , 778-780, 238-242	0.4	2
256	Fracture property and quantitative strain evaluation of hetero-epitaxial single crystal 3C-SiC membrane. <i>Materials Research Express</i> , 2014 , 1, 015912	1.7	4
255	Evaluation of Mechanical and Optical Properties of Hetero-Epitaxial Single Crystal 3C-SiC Squared-Membrane. <i>Materials Science Forum</i> , 2014 , 778-780, 457-460	0.4	3
254	Monte Carlo Study of the Hetero-Polytypical Growth of Cubic on Hexagonal Silicon Carbide Polytypes. <i>Materials Science Forum</i> , 2013 , 740-742, 295-300	0.4	1
253	Fast Growth Rate Epitaxy by Chloride Precursors. <i>Materials Science Forum</i> , 2013 , 740-742, 167-172	0.4	5
252	Micro-Raman analysis and finite-element modeling of 3 C-SiC microstructures. <i>Journal of Raman Spectroscopy</i> , 2013 , 44, 299-306	2.3	12
251	Effects of Al Ion Implantation on 3C-SiC Crystal Structure. <i>Materials Science Forum</i> , 2013 , 740-742, 613-616		
250	Patterned substrate with inverted silicon pyramids for 3C-SiC epitaxial growth: A comparison with conventional (001) Si substrate. <i>Journal of Materials Research</i> , 2013 , 28, 94-103	2.5	12
249	Stress Relaxation Study in 3C-SiC Microstructures by Micro-Raman Analysis and Finite Element Modeling. <i>Materials Science Forum</i> , 2013 , 740-742, 673-676	0.4	
248	3C-SiC Growth on (001) Si Substrates by Using a Multilayer Buffer. <i>Materials Science Forum</i> , 2013 , 740-742, 263-266	0.4	1
247	Post-Growth Process Effect on Hetero-Epitaxial 3C-SiC Wafer Bow and Residual Stress. <i>Materials Science Forum</i> , 2013 , 740-742, 301-305	0.4	1

246	Study of the Effects of Growth Rate, Miscut Direction and Postgrowth Argon Annealing on the Surface Morphology of Homoepitaxially Grown 4H Silicon Carbide Films. <i>Materials Science Forum</i> , 2013 , 740-742, 229-234	0.4	8
245	High performance SiC detectors for MeV ion beams generated by intense pulsed laser plasmas. <i>Journal of Materials Research</i> , 2013 , 28, 87-93	2.5	56
244	Stress nature investigation on heteroepitaxial 3C-SiC film on (100) Si substrates. <i>Journal of Materials Research</i> , 2013 , 28, 129-135	2.5	6
243	Correlation between macroscopic and microscopic stress fields: Application to the 3C-SiC/Si heteroepitaxy. <i>Journal of Materials Research</i> , 2013 , 28, 104-112	2.5	4
242	Introduction to Silicon Carbide [Materials, Processing and Devices] ADDENDUM. <i>Journal of Materials Research</i> , 2013 , 28, 786-786	2.5	1
241	Morphology and distribution of carbon nanostructures in a deposit produced by arc discharge in liquid nitrogen. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , 2012 , 44, 1005-1008	3	4
240	Stress fields analysis in 3C-SiC free-standing microstructures by micro-Raman spectroscopy. <i>Thin Solid Films</i> , 2012 , 522, 20-22	2.2	13
239	Large area optical characterization of 3 and 4 inches 4H-SiC wafers. <i>Thin Solid Films</i> , 2012 , 522, 30-32	2.2	2
238	Study of microstructure deflections and film/substrate curvature under generalized stress fields and mechanical properties. <i>Thin Solid Films</i> , 2012 , 522, 26-29	2.2	7
237	Crystal recovery from Al-implantation induced damaging in 3C-SiC films. <i>Physica Status Solidi - Rapid Research Letters</i> , 2012 , 6, 226-228	2.5	2
236	Chloride-Based CVD of 4H-SiC at High Growth Rates on Substrates with Different Off-Angles. <i>Materials Science Forum</i> , 2012 , 717-720, 113-116	0.4	2
235	Extended Characterization of the Stress Fields in the Heteroepitaxial Growth of 3C-SiC on Silicon for Sensors and Device Applications. <i>Materials Science Forum</i> , 2012 , 717-720, 517-520	0.4	3
234	Micro-Raman Analysis of a Micromachined 3C-SiC Cantilever. <i>Materials Science Forum</i> , 2012 , 717-720, 525-528	0.4	1
233	Mechanical Proprieties and Residual Stress Evaluation on Heteroepitaxial 3C-SiC/Si for MEMS Application. <i>Materials Science Forum</i> , 2012 , 711, 51-54	0.4	4
232	Stress Evaluation on Hetero-Epitaxial 3C-SiC Film on (100) Si Substrates. <i>Materials Science Forum</i> , 2012 , 717-720, 521-524	0.4	3
231	Consideration on the Thermal Expansion of 3C-SiC Epitaxial Layer on Si Substrates. <i>Materials Science Forum</i> , 2012 , 711, 31-34	0.4	1
230	Electron backscattering from stacking faults in SiC by means of ab initio quantum transport calculations. <i>Physical Review B</i> , 2012 , 85,	3.3	27
229	Study of the Impact of Growth and Post-Growth Processes on the Surface Morphology of 4H Silicon Carbide Films. <i>Materials Science Forum</i> , 2012 , 717-720, 149-152	0.4	2

228	SiC Films and Coatings 2012 , 17-61		8
227	Structural Characterization of Heteroepitaxial 3C-SiC. <i>Materials Science Forum</i> , 2012 , 711, 27-30	0.4	5
226	Strain Field Analysis of 3C-SiC Free-Standing Microstructures by Micro-Raman and Theoretical Modelling. <i>Materials Science Forum</i> , 2012 , 711, 55-60	0.4	3
225	Growth and processing of heteroepitaxial 3C-SiC films for electronic devices applications. <i>Materials Research Society Symposia Proceedings</i> , 2012 , 1433, 25		2
224	Wafer Cut Effect on Hetero-Epitaxial 3C-SiC Film for MEMS Application. <i>Electrochemical and Solid-State Letters</i> , 2012 , 15, H182		6
223	On the Step Bunching Phenomena Observed on Etched and Homoepitaxially Grown 4H Silicon Carbide. <i>Materials Science Forum</i> , 2011 , 679-680, 358-361	0.4	10
222	Study of the connection between stacking faults evolution and step kinetics in misoriented 4H-SiC epitaxial growths. <i>Surface Science</i> , 2011 , 605, L67-L69	1.8	8
221	Structural and electronic characterization of (2,33) bar-shaped stacking fault in 4H-SiC epitaxial layers. <i>Applied Physics Letters</i> , 2011 , 98, 051915	3.4	16
220	First Principles Investigation on the Modifications of the 4H-SiC Band Structure Due to the (4,4) and (3,5) Stacking Faults. <i>Applied Physics Express</i> , 2011 , 4, 025802	2.4	19
219	Advanced Residual Stress Analysis and FEM Simulation on Heteroepitaxial 3C-SiC for MEMS Application. <i>Journal of Microelectromechanical Systems</i> , 2011 , 20, 745-752	2.5	45
218	High Power Density UV Optical Stress for Quality Evaluation of 4H-SiC Epitaxial Layers. <i>Electrochemical and Solid-State Letters</i> , 2011 , 14, H457		
217	Raman Stress Characterization of Hetero-Epitaxial 3C-SiC Free Standing Structures. <i>Materials Science Forum</i> , 2011 , 679-680, 141-144	0.4	7
216	Evolution of Extended Defects during Epitaxial Growths: A Monte Carlo Study. <i>Materials Science Forum</i> , 2011 , 679-680, 48-54	0.4	1
215	Publisher's Note: Defect Influence on Heteroepitaxial 3C-SiC Young's Modulus [Electrochem. Solid-State Lett., 14, H161 (2011)]. <i>Electrochemical and Solid-State Letters</i> , 2011 , 14, S3		4
214	Complete Determination of the Local Stress Field in Epitaxial Thin Films Using Single Microstructure. <i>Materials Science Forum</i> , 2011 , 679-680, 213-216	0.4	10
213	Advanced Stress Analysis by Micro-Structures Realization on High Quality Hetero-Epitaxial 3C-SiC for MEMS Application. <i>Materials Science Forum</i> , 2011 , 679-680, 133-136	0.4	6
212	Raman Study of Bulk Mobility in 3C-SiC Heteroepitaxy. <i>Materials Science Forum</i> , 2011 , 679-680, 221-224	0.4	4
211	Defect Influence on Heteroepitaxial 3C-SiC Young's Modulus. <i>Electrochemical and Solid-State Letters</i> , 2011 , 14, H161		33

210	3C-SiC Film Growth on Si Substrates. <i>ECS Transactions</i> , 2011 , 35, 99-116	1	28
209	Advanced Residual Stress Analysis on the Heteroepitaxial Growth of 3C-SiC/Si for MEMS Application. <i>ECS Transactions</i> , 2011 , 35, 123-131	1	1
208	Reduction of the Surface Density of Single Shockley Faults by TCS Growth Process. <i>Materials Science Forum</i> , 2011 , 679-680, 67-70	0.4	9
207	(Invited) High Quality 3C-SiC for MOS Applications. <i>ECS Transactions</i> , 2011 , 41, 273-282	1	3
206	Study of the Evolution of Basal Plane Dislocations during Epitaxial Growth: Role of the Surface Kinetics. <i>Materials Science Forum</i> , 2010 , 645-648, 539-542	0.4	8
205	Raman Characterization of Doped 3C-SiC/Si for Different Silicon Substrates and C/Si Ratios. <i>Materials Science Forum</i> , 2010 , 645-648, 255-258	0.4	17
204	Bow in 6 Inch High-Quality Off-Axis (111) 3C-SiC Films. <i>Materials Science Forum</i> , 2010 , 645-648, 167-170	0.4	2
203	Single Shockley Faults Enlargement during Micro-Photoluminescence Defects Mapping. <i>Materials Science Forum</i> , 2010 , 645-648, 555-558	0.4	7
202	Systematic first principles calculations of the effects of stacking faults defects on the 4H-SiC band structure. <i>Materials Research Society Symposia Proceedings</i> , 2010 , 1246, 1		1
201	3C-SiC Heteroepitaxial Growth on Inverted Silicon Pyramids (ISP). <i>Materials Science Forum</i> , 2010 , 645-648, 135-138	0.4	8
200	Residual Stress Measurement and Simulation of 3C-SiC Single and Poly Crystal Cantilevers. <i>Materials Science Forum</i> , 2010 , 645-648, 865-868	0.4	3
199	Single Shockley faults evolution under UV optical pumping. <i>Materials Research Society Symposia Proceedings</i> , 2010 , 1246, 1		3
198	A Study of Structural Defects in 3C-SiC Hetero-Epitaxial Films. <i>Materials Science Forum</i> , 2010 , 645-648, 371-374	0.4	2
197	Systematic First Principles Calculations of the Effects of Stacking Fault Defects on the 4H-SiC Band Structure. <i>Materials Science Forum</i> , 2010 , 645-648, 283-286	0.4	8
196	Growth Rate Effect on 3C-SiC Film Residual Stress on (100) Si Substrates. <i>Materials Science Forum</i> , 2010 , 645-648, 143-146	0.4	21
195	Evolution of Stacking Faults Defects During Epitaxial Growths: Role of Surface Kinetics.. <i>Materials Research Society Symposia Proceedings</i> , 2010 , 1246, 1		
194	Microtwin reduction in 3C-SiC heteroepitaxy. <i>Applied Physics Letters</i> , 2010 , 97, 181916	3.4	14
193	Optical investigation of bulk electron mobility in 3C-SiC films on Si substrates. <i>Applied Physics Letters</i> , 2010 , 97, 142103	3.4	11

192	Low Stress Heteroepitaxial 3C-SiC Films Characterized by Microstructure Fabrication and Finite Elements Analysis. <i>Journal of the Electrochemical Society</i> , 2010 , 157, H438	3.9	20
191	Monte Carlo study of morphological surface instabilities during misoriented epitaxial growth of cubic and hexagonal polytypes 2010 ,		2
190	Multiscale simulation for epitaxial silicon carbide growth by chlorides route. <i>Thin Solid Films</i> , 2010 , 518, S6-S11	2.2	3
189	Extended study of the step-bunching mechanism during the homoepitaxial growth of SiC. <i>Thin Solid Films</i> , 2010 , 518, S159-S161	2.2	20
188	High-quality 6inch (111) 3C-SiC films grown on off-axis (111) Si substrates. <i>Thin Solid Films</i> , 2010 , 518, S165-S169	2.2	55
187	Stacking faults evolution during epitaxial growths: Role of surface the kinetics. <i>Surface Science</i> , 2010 , 604, 939-942	1.8	17
186	Preferential oxidation of stacking faults in epitaxial off-axis (111) 3C-SiC films. <i>Applied Physics Letters</i> , 2009 , 95, 111905	3.4	21
185	Heteroepitaxy of 3C-SiC on different on-axis oriented silicon substrates. <i>Journal of Applied Physics</i> , 2009 , 105, 084910	2.5	55
184	Defects in High Energy Ion Irradiated 4H-SiC. <i>Materials Science Forum</i> , 2009 , 615-617, 397-400	0.4	5
183	Atomistic and Continuum Simulations of the Homo-Epitaxial Growth of SiC. <i>Materials Science Forum</i> , 2009 , 615-617, 73-76	0.4	6
182	Thick Epitaxial Layers Growth by Chlorine Addition. <i>Materials Science Forum</i> , 2009 , 615-617, 55-60	0.4	15
181	Residual Stress Measurement on Hetero-Epitaxial 3C-SiC Films. <i>Materials Science Forum</i> , 2009 , 615-617, 629-632	0.4	
180	Towards Large Area (111)3C-SiC Films Grown on Off-Oriented (111)Si. <i>Materials Science Forum</i> , 2009 , 615-617, 149-152	0.4	4
179	High Quality Single Crystal 3C-SiC(111) Films Grown on Si(111). <i>Materials Science Forum</i> , 2009 , 615-617, 145-148	0.4	13
178	Extended Study of the Step-Bunching Mechanism during the Homoepitaxial Growth of SiC. <i>Materials Science Forum</i> , 2009 , 615-617, 117-120	0.4	2
177	Monte Carlo study of the step flow to island nucleation transition for close packed structures. <i>Surface Science</i> , 2009 , 603, 2226-2229	1.8	15
176	Effect of the miscut direction in (111) 3C-SiC film growth on off-axis (111)Si. <i>Applied Physics Letters</i> , 2009 , 94, 101907	3.4	26
175	Structural defects in (100) 3C-SiC heteroepitaxy: Influence of the buffer layer morphology on generation and propagation of stacking faults and microtwins. <i>Diamond and Related Materials</i> , 2009 , 18, 1440-1449	3.5	43

174	Low temperature reaction of point defects in ion irradiated 4H-SiC. <i>Diamond and Related Materials</i> , 2009 , 18, 39-42	3.5	3
173	Heteroepitaxial growth of (111) 3C-SiC on (110) Si substrate by second order twins. <i>Applied Physics Letters</i> , 2008 , 92, 224102	3.4	19
172	Theoretical Monte Carlo Study of the Formation and Evolution of Defects in the Homoepitaxial Growth of SiC. <i>Materials Science Forum</i> , 2008 , 600-603, 135-138	0.4	16
171	3C-SiC Hetero-Epitaxial Films for Sensors Fabrication. <i>Advances in Science and Technology</i> , 2008 , 54, 411-415	0.15	10
170	Thin SiC-4H Epitaxial Layer Growth by Trichlorosilane (TCS) as Silicon Precursor with Very Abrupt Junctions. <i>Materials Science Forum</i> , 2008 , 600-603, 127-130	0.4	6
169	3C-SiC Heteroepitaxy on (100), (111) and (110) Si Using Trichlorosilane (TCS) as the Silicon Precursor.. <i>Materials Science Forum</i> , 2008 , 600-603, 243-246	0.4	5
168	Void Formation in Differently Oriented Si in the Early Stage of SiC Growth. <i>Materials Science Forum</i> , 2008 , 600-603, 215-218	0.4	
167	Compensation Effects in 7 MeV C Irradiated n-Doped 4H-SiC. <i>Materials Science Forum</i> , 2008 , 600-603, 619-622	0.4	3
166	SiC-4H Epitaxial Layer Growth by Trichlorosilane (TCS) as Silicon Precursor at Very High Growth Rate. <i>Materials Science Forum</i> , 2008 , 600-603, 123-126	0.4	8
165	Growth of 3C-SiC on Si: Influence of Process Pressure. <i>Materials Science Forum</i> , 2008 , 600-603, 211-214	0.4	2
164	Electrical properties of high energy ion irradiated 4H-SiC Schottky diodes. <i>Journal of Applied Physics</i> , 2008 , 104, 093711	2.5	19
163	Defect formation and evolution in the step-flow growth of silicon carbide: A Monte Carlo study. <i>Journal of Crystal Growth</i> , 2008 , 310, 971-975	1.6	27
162	4H-SiC epitaxial layer growth by trichlorosilane (TCS). <i>Journal of Crystal Growth</i> , 2008 , 311, 107-113	1.6	58
161	Point defect production efficiency in ion irradiated 4H-SiC. <i>Nuclear Instruments & Methods in Physics Research B</i> , 2007 , 257, 279-282	1.2	0
160	A kinetic Monte Carlo method on super-lattices for the study of the defect formation in the growth of close packed structures. <i>Journal of Computational Physics</i> , 2007 , 227, 1075-1093	4.1	41
159	Effect of Mo interlayer on thermal stability of polycrystalline NiSi thin films. <i>Journal of Applied Physics</i> , 2007 , 101, 063544	2.5	1
158	Optical and electrical properties of 4H-SiC epitaxial layer grown with HCl addition. <i>Journal of Applied Physics</i> , 2007 , 102, 043523	2.5	16
157	Thin crystalline 3C-SiC layer growth through carbonization of differently oriented Si substrates. <i>Journal of Applied Physics</i> , 2007 , 102, 023518	2.5	59

156	Carbonization Study of Different Silicon Orientations. <i>Materials Science Forum</i> , 2007 , 556-557, 171-174	0.4	3
155	Very High Growth Rate Epitaxy Processes with Chlorine Addition. <i>Materials Science Forum</i> , 2007 , 556-557, 157-160	0.4	15
154	Film Morphology and Process Conditions in Epitaxial Silicon Carbide Growth via Chlorides Route. <i>Materials Science Forum</i> , 2007 , 556-557, 93-96	0.4	6
153	Optimisation of Epitaxial Layer Growth with HCl Addition by Optical and Electrical Characterization. <i>Materials Science Forum</i> , 2007 , 556-557, 137-140	0.4	3
152	4H SiC Epitaxial Growth with Chlorine Addition. <i>Chemical Vapor Deposition</i> , 2006 , 12, 509-515		77
151	High Growth Rate Process in a SiC Horizontal Reactor with HCl Addition: Structural and Electrical Characterization. <i>Materials Research Society Symposia Proceedings</i> , 2006 , 911, 1		
150	Effect of Dopant Concentration on High Voltage 4H-SiC Schottky Diodes. <i>Materials Research Society Symposia Proceedings</i> , 2006 , 911, 2		2
149	Optimisation of Epitaxial Layer Growth by Schottky Diodes Electrical Characterization. <i>Materials Science Forum</i> , 2006 , 527-529, 199-202	0.4	0
148	OHMIC CONTACTS TO. <i>Selected Topics in Electornics and Systems</i> , 2006 , 77-116	0	4
147	SiC-4H Epitaxial Layer Growth Using Trichlorosilane (TCS) as Silicon Precursor. <i>Materials Science Forum</i> , 2006 , 527-529, 179-182	0.4	23
146	Epitaxial Layers Grown with HCl Addition: A Comparison with the Standard Process. <i>Materials Science Forum</i> , 2006 , 527-529, 163-166	0.4	13
145	Heteroepitaxial Growth of 3C-SiC on Silicon-Porous Silicon-Silicon (SPS) Substrates. <i>ECS Transactions</i> , 2006 , 3, 287-298	1	5
144	Temperature dependence of the c-axis drift mobility in 4H-SiC. <i>Microelectronic Engineering</i> , 2006 , 83, 45-47	2.5	5
143	High growth rate process in a SiC horizontal CVD reactor using HCl. <i>Microelectronic Engineering</i> , 2006 , 83, 48-50	2.5	15
142	Effects of implantation defects on the carrier concentration of 6H-SiC. <i>Applied Physics A: Materials Science and Processing</i> , 2006 , 82, 543-547	2.6	2
141	Effects of annealing temperature on the degree of inhomogeneity of nickel-silicide/SiC Schottky barrier. <i>Journal of Applied Physics</i> , 2005 , 98, 023713	2.5	52
140	Ion irradiation of inhomogeneous Schottky barriers on silicon carbide. <i>Journal of Applied Physics</i> , 2005 , 97, 123502	2.5	24
139	Temperature Stability of Breakdown Voltage on SiC Power Schottky Diodes with Different Barrier Heights. <i>Materials Science Forum</i> , 2005 , 483-485, 933-936	0.4	5

138	Ion-Beam Induced Modifications of Titanium Schottky Barrier on 4H-SiC. <i>Materials Science Forum</i> , 2005 , 483-485, 729-732	0.4	1
137	Defect Evolution in Ion Irradiated 6H-SiC Epitaxial Layers. <i>Materials Science Forum</i> , 2005 , 483-485, 485-488	0.4	1
136	Effects of Epitaxial Layer Growth Parameters on the Defect Density and on the Electrical Characteristics of Schottky Diodes. <i>Materials Science Forum</i> , 2005 , 483-485, 429-432	0.4	1
135	New Achievements on CVD Based Methods for SiC Epitaxial Growth. <i>Materials Science Forum</i> , 2005 , 483-485, 67-72	0.4	46
134	Drift mobility in 4H-SiC Schottky diodes. <i>Applied Physics Letters</i> , 2005 , 87, 142105	3.4	17
133	OHMIC CONTACTS TO SiC. <i>International Journal of High Speed Electronics and Systems</i> , 2005 , 15, 781-820	0.5	65
132	Effect of a Ti Cap Layer on the Diffusion of Co Atoms during CoSi ₂ Reaction. <i>Electrochemical and Solid-State Letters</i> , 2005 , 8, G47		6
131	Silicon Carbide: Defects and Devices. <i>Solid State Phenomena</i> , 2005 , 108-109, 663-670	0.4	4
130	Environment influence on Ti diffusion and layer degradation of a SiC/Ni ₂ Si/TiW/Au contact structure. <i>Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena</i> , 2004 , 22, 966		7
129	C49-C54 phase transition in nanometric titanium disilicide grains. <i>Journal of Applied Physics</i> , 2004 , 95, 1977-1985	2.5	3
128	Investigations of transient phase formation in Ti/Si thin film reaction. <i>Journal of Applied Physics</i> , 2004 , 96, 361-368	2.5	12
127	Influence of defects on the kinetic of C49-C54 TiSi ₂ transformation. <i>Applied Physics Letters</i> , 2004 , 85, 5577-5579	3.4	2
126	Tailoring the Ti/SiC Schottky barrier by ion irradiation. <i>Applied Physics Letters</i> , 2004 , 85, 6152-6154	3.4	21
125	Effects of Thermal Treatments on the Structural and Electrical Properties of Ni/Ti Bilayers Schottky Contacts on 6H-SiC. <i>Materials Science Forum</i> , 2004 , 457-460, 865-868	0.4	4
124	Defects in He ⁺ Irradiated 6H-SiC Probed by DLTS and LTPL Measurements. <i>Materials Science Forum</i> , 2004 , 457-460, 493-496	0.4	2
123	Schottky-Ohmic Transition in Nickel Silicide/SiC-4H System: the Effect of Non Uniform Schottky Barrier. <i>Materials Science Forum</i> , 2004 , 457-460, 861-864	0.4	5
122	Study of TiW/Au Thin Films Metallization Stack for High Temperature and Harsh Environment Devices on 6H Silicon Carbide. <i>Materials Science Forum</i> , 2004 , 457-460, 873-876	0.4	6
121	Electrical Characterization of Inhomogeneous Ni ₂ /Si/SiC Schottky Contacts. <i>Materials Science Forum</i> , 2004 , 457-460, 869-872	0.4	1

120	Structural characterization and oxygen concentration profiling of a Co/Si multilayer structure. <i>Nuclear Instruments & Methods in Physics Research B</i> , 2004 , 219-220, 732-736	1.2	
119	Structural and electrical properties of Ni/Ti Schottky contacts on silicon carbide upon thermal annealing. <i>Journal of Applied Physics</i> , 2004 , 96, 4313-4318	2.5	60
118	Time resolved CoSi ₂ reaction in presence of Ti and TiN cap layers. <i>Materials Science and Engineering B: Solid-State Materials for Advanced Technology</i> , 2004 , 114-115, 232-235	3.1	2
117	Highly reproducible ideal SiC Schottky rectifiers: effects of surface preparation and thermal annealing on the Ni/6H-SiC barrier height. <i>Applied Physics A: Materials Science and Processing</i> , 2003 , 77, 827-833	2.6	73
116	Silicon carbide pinch rectifiers using a dual-metal Ti-Ni/sub 2/Si Schottky barrier. <i>IEEE Transactions on Electron Devices</i> , 2003 , 50, 1741-1747	2.9	21
115	Thermal oxidation of As and Ge implanted Si(). <i>Surface Science</i> , 2003 , 532-535, 746-753	1.8	7
114	First stages of silicidation in Ti/Si thin films. <i>Microelectronic Engineering</i> , 2003 , 70, 166-173	2.5	4
113	C49 defect influence on the C49↔54 transition. <i>Microelectronic Engineering</i> , 2003 , 70, 215-219	2.5	1
112	Time resolved study on Co/Ni/a-Si phase transition during isothermal annealing at 400 °C. <i>Microelectronic Engineering</i> , 2003 , 70, 191-195	2.5	1
111	Schottky-Ohmic transition in nickel silicide/SiC-4H system: is it really a solved problem?. <i>Microelectronic Engineering</i> , 2003 , 70, 519-523	2.5	67
110	Dual metal SiC Schottky rectifiers with low power dissipation. <i>Microelectronic Engineering</i> , 2003 , 70, 524-538	2.5	9
109	Richardson's constant in inhomogeneous silicon carbide Schottky contacts. <i>Journal of Applied Physics</i> , 2003 , 93, 9137-9144	2.5	201
108	Temperature dependence of the c-axis mobility in 6H-SiC Schottky diodes. <i>Applied Physics Letters</i> , 2003 , 83, 4181-4183	3.4	21
107	Comparison between Different Schottky Diode Edge Termination Structures: Simulations and Experimental Results. <i>Materials Science Forum</i> , 2003 , 433-436, 827-830	0.4	6
106	Activation Study of Implanted N+ in 6H-SiC by Scanning Capacitance Microscopy. <i>Materials Science Forum</i> , 2003 , 433-436, 375-378	0.4	9
105	Low Power Dissipation SiC Schottky Rectifiers with a Dual-Metal Planar Structure. <i>Materials Science Forum</i> , 2003 , 433-436, 819-822	0.4	0
104	Schottky-Ohmic Transition in Nickel Silicide/SiC System: Is it Really a Solved Problem?. <i>Materials Science Forum</i> , 2003 , 433-436, 721-724	0.4	16
103	Thermal expansion and stress development in the first stages of silicidation in Ti/Si thin films. <i>Journal of Applied Physics</i> , 2003 , 94, 7083-7090	2.5	8

102	High-resolution investigation of atomic interdiffusion during Co/Ni/Si phase transition. <i>Journal of Applied Physics</i> , 2003 , 94, 231-237	2.5	13
101	Correlation between microstructure control, density and diffusion barrier properties of TiN(O) films. <i>Microelectronic Engineering</i> , 2002 , 60, 81-87	2.5	8
100	Effects of a Ta interlayer on the titanium silicide reaction: C40 formation and scalability of the TiSi ₂ process. <i>Microelectronic Engineering</i> , 2002 , 60, 197-203	2.5	2
99	Structural and electrical characterisation of titanium and nickel silicide contacts on silicon carbide. <i>Microelectronic Engineering</i> , 2002 , 60, 269-282	2.5	114
98	Electrical properties of TiSi ₂ clusters in poly Si. <i>Microelectronic Engineering</i> , 2002 , 64, 197-204	2.5	2
97	C49 \leftrightarrow C54 phase transition in nanometric titanium disilicide nanograins. <i>Microelectronic Engineering</i> , 2002 , 64, 189-196	2.5	3
96	Study of CoSi ₂ thermal stability improved by interfacial cavities. <i>Microelectronic Engineering</i> , 2002 , 64, 151-156	2.5	2
95	Origin of the C49 \leftrightarrow C54 volume anomaly in TiSi ₂ thin films: an in-situ XRD and TEM analysis. <i>Microelectronic Engineering</i> , 2002 , 64, 181-187	2.5	3
94	TEM analysis of an additional metal-rich component at the C49 \leftrightarrow C54 transformation in Ti/Si thin films capped with TiN. <i>Thin Solid Films</i> , 2002 , 408, 123-127	2.2	10
93	Electrical resistivity and Hall coefficient of C49, C40, and C54 TiSi ₂ thin-film phases. <i>Journal of Applied Physics</i> , 2002 , 92, 3147-3151	2.5	11
92	Reaction of the Si/Ta/Ti system: C40 TiSi ₂ phase formation and in situ kinetics. <i>Journal of Applied Physics</i> , 2002 , 91, 633-638	2.5	8
91	Effects of N-induced heterogeneous nucleation and growth of cavities at the CoSi ₂ /polycrystallineSilicon interface. <i>Applied Physics Letters</i> , 2002 , 81, 55-57	3.4	9
90	Direct measurement of the growth rate during the C49 to C54 transformation in TiSi ₂ : Activation energy. <i>Journal of Applied Physics</i> , 2002 , 92, 627-628	2.5	13
89	Thermal stability of SiO ₂ /CoSi ₂ /polysilicon multilayer structures improved by cavity formation. <i>Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena</i> , 2002 , 20, 880		
88	Quantitative High-Resolution Two-Dimensional Profiling of SiC by Scanning Capacitance Microscopy. <i>Materials Science Forum</i> , 2002 , 389-393, 655-658	0.4	
87	Electrical Characterization of Nickel Silicide Contacts on Silicon Carbide. <i>Materials Science Forum</i> , 2002 , 389-393, 893-896	0.4	2
86	Thermal oxidation of Si (001) single crystal implanted with Ge ions. <i>Journal of Applied Physics</i> , 2002 , 91, 6754	2.5	10
85	Reduction of the power dissipation in silicon carbide Schottky rectifiers by a dual-metal planar structure. <i>Applied Physics Letters</i> , 2002 , 81, 1125-1127	3.4	7

84	Kinetics of the C49 \rightarrow C54 transformation by micro-Raman imaging. <i>Microelectronic Engineering</i> , 2001 , 55, 109-114	2.5	4
83	Structural investigations of the C49 \rightarrow C54 transformation in TiSi ₂ thin films. <i>Microelectronic Engineering</i> , 2001 , 55, 115-122	2.5	6
82	Effect of a thin Ta layer on the C49 \rightarrow C54 transition. <i>Microelectronic Engineering</i> , 2001 , 55, 123-128	2.5	4
81	Structural characterisation of titanium silicon carbide reaction. <i>Microelectronic Engineering</i> , 2001 , 55, 375-381	2.5	23
80	Dopant profile measurements in ion implanted 6H β SiC by scanning capacitance microscopy. <i>Applied Surface Science</i> , 2001 , 184, 183-189	6.7	9
79	Structural properties of SiO ₂ films prepared by plasma-enhanced chemical vapor deposition. <i>Materials Science in Semiconductor Processing</i> , 2001 , 4, 43-46	4.3	15
78	Oxidation of ion implanted silicon carbide. <i>Materials Science in Semiconductor Processing</i> , 2001 , 4, 345-349	4.3	9
77	Structural relationship of polycrystalline cobalt silicide lines to (001) silicon substrate and their thermal stability. <i>Microelectronic Engineering</i> , 2001 , 55, 163-169	2.5	7
76	Improvement of high temperature stability of nickel contacts on n-type 6H β SiC. <i>Applied Surface Science</i> , 2001 , 184, 295-298	6.7	58
75	Ion-Irradiation Effect on the Ni/SiC Interface Reaction. <i>Materials Science Forum</i> , 2001 , 353-356, 255-258	0.4	4
74	Defect-induced tetragonalization of the orthorhombic TiSi ₂ C49 phase: X-ray diffraction and first principles calculations. <i>Applied Physics Letters</i> , 2001 , 78, 739-741	3.4	11
73	Simulation of the transformation from the C49 to the C54 phase of TiSi ₂ in blanket films and narrow conductors. <i>Applied Physics Letters</i> , 2001 , 78, 1514-1516	3.4	4
72	In situ investigations of the metal/silicon reaction in Ti/Si thin films capped with TiN: Volumetric analysis of the C49 \rightarrow C54 transformation. <i>Applied Physics Letters</i> , 2001 , 79, 2184-2186	3.4	10
71	Improvement of CoSi ₂ thermal stability by cavity formation. <i>Applied Physics Letters</i> , 2001 , 79, 3419-3421	3.4	8
70	Formation of the TiSi ₂ C40 as an intermediate phase during the reaction of the Si/Ta/Ti system. <i>Applied Physics Letters</i> , 2001 , 78, 1864-1866	3.4	14
69	X-Ray Reflectivity Study of the Structural Properties of SiO ₂ and SiOF Thin Films. <i>Journal of the Electrochemical Society</i> , 2001 , 148, F221	3.9	5
68	Effects of a Ta Interlayer on the Titanium Silicide Reaction: C40 Formation and Higher Scalability of the TiSi ₂ Process. <i>Materials Research Society Symposia Proceedings</i> , 2001 , 670, 1		
67	Structural and Electrical Characterisation of Nickel Silicides Contacts on Silicon Carbide. <i>Materials Research Society Symposia Proceedings</i> , 2001 , 680, 1		

66	Enhanced oxidation of ion-damaged 6H-SiC. <i>The Philosophical Magazine: Physics of Condensed Matter B, Statistical Mechanics, Electronic, Optical and Magnetic Properties</i> , 2000 , 80, 661-667		3
65	Effect of a thin Ta layer on the C49-C54 transition. <i>Materials Research Society Symposia Proceedings</i> , 2000 , 611, 1		
64	Investigation on C54 nucleation and growth by micro-Raman imaging. <i>Materials Research Society Symposia Proceedings</i> , 2000 , 611, 1		
63	Structural properties of fluorinated SiO ₂ thin films. <i>Microelectronic Engineering</i> , 2000 , 50, 67-74	2.5	18
62	Determination of C54 nucleation site density in narrow stripes by sheet resistance measurements and Raman spectroscopy. <i>Microelectronic Engineering</i> , 2000 , 50, 139-145	2.5	7
61	Investigation of C49 \rightarrow C54 TiSi ₂ transformation kinetics. <i>Microelectronic Engineering</i> , 2000 , 50, 153-158	2.5	7
60	Effect of lateral dimensional scaling on the thermal stability of poly-CoSi ₂ reacted on Si (001). <i>Microelectronic Engineering</i> , 2000 , 50, 179-186	2.5	
59	Thermal Oxidation of High Dose Aluminum Implanted Silicon. <i>Journal of the Electrochemical Society</i> , 2000 , 147, 2762	3.9	2
58	Effect of lateral dimensional scaling on the thermal stability of thin CoSi ₂ layers reacted on polycrystalline silicon. <i>Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena</i> , 2000 , 18, 717		4
57	Role of the substrate in the C49 \rightarrow C54 transformation of TiSi ₂ . <i>Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena</i> , 2000 , 18, 721		11
56	Nucleation and growth of C54 grains into C49 TiSi ₂ thin films monitored by micro-Raman imaging. <i>Journal of Applied Physics</i> , 2000 , 88, 7013-7019	2.5	18
55	Reaction and thermal stability of cobalt disilicide on polysilicon resulting from a Si/Ti/Co multilayer system. <i>Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena</i> , 1999 , 17, 1448		7
54	Structural relationship of polycrystalline cobalt silicide lines to (001) silicon substrate. <i>Applied Physics Letters</i> , 1999 , 75, 2924-2926	3.4	4
53	Thermal stability of cobalt silicide stripes on Si (001). <i>Journal of Applied Physics</i> , 1999 , 86, 3089-3095	2.5	20
52	Cobalt silicide thermal stability: from blanket thin film to submicrometer lines. <i>Solid-State Electronics</i> , 1999 , 43, 1039-1044	1.7	5
51	Texturing, surface energetics and morphology in the C49 \rightarrow C54 transformation of TiSi ₂ . <i>Solid-State Electronics</i> , 1999 , 43, 1069-1074	1.7	4
50	Estimation of The Critical Radius for The Nucleation of the C54 Phase in C49 TiSi ₂ : Role of The Difference in Density. <i>Materials Research Society Symposia Proceedings</i> , 1999 , 580, 129		2
49	Thermal stability of thin CoSi ₂ layers on polysilicon implanted with As, BF ₂ , and Si. <i>Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena</i> , 1998 , 16, 1129		20

48	Roughness of thermal oxide layers grown on ion implanted silicon wafers. <i>Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena</i> , 1998 , 16, 619		13
47	Arsenic redistribution at the SiO ₂ /Si interface during oxidation of implanted silicon. <i>Physical Review B</i> , 1998 , 58, 10990-10999	3.3	11
46	Effect of the linewidth reduction on the characteristic time spread in C49-C54 phase transition. <i>Applied Physics Letters</i> , 1998 , 73, 3863-3865	3.4	20
45	Precipitation of As in thermally oxidized ion-implanted Si crystals. <i>Applied Physics Letters</i> , 1998 , 73, 2633-2635	3.4	8
44	Kinetics of the C49-C54 transformation in patterned and blanket TiSi ₂ films: a comparison.. <i>Materials Research Society Symposia Proceedings</i> , 1998 , 514, 219		3
43	Effect of lateral dimension scaling on thermal stability of thin CoSi ₂ layers on polysilicon implanted with Si. <i>Materials Research Society Symposia Proceedings</i> , 1998 , 514, 381		2
42	Reduction of the C49-C54 TiSi ₂ phase transformation temperature by reactive Ti deposition. <i>Europhysics Letters</i> , 1997 , 40, 581-586	1.6	11
41	Hole mobility in aluminium implanted silicon. <i>Semiconductor Science and Technology</i> , 1997 , 12, 1433-1437	1.8	6
40	Structure, Morphology and Kinetics of the C49 to C54 Phase Transformation In Tisi ₂ Thin Films. <i>Materials Research Society Symposia Proceedings</i> , 1997 , 481, 593		
39	Electrical characterization of ultra-shallow junctions formed by diffusion from a CoSi ₂ /sub 2/ layer. <i>IEEE Transactions on Electron Devices</i> , 1997 , 44, 526-534	2.9	30
38	Kinetics of the C49-C54 phase transition in TiSi ₂ : New indications from sheet resistance, infrared spectroscopy and molecular dynamics simulations. <i>Microelectronic Engineering</i> , 1997 , 37-38, 441-448	2.5	7
37	Thermal stability of thin CoSi ₂ layers grown on amorphous silicon. <i>Microelectronic Engineering</i> , 1997 , 37-38, 475-481	2.5	3
36	EXAFS investigation of Co sites in CoSi ₂ film grown by ion beam-assisted deposition. <i>Microelectronic Engineering</i> , 1997 , 37-38, 491-497	2.5	3
35	Two-dimensional junction profiling by selective chemical etching: Applications to electron device characterization. <i>Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena</i> , 1996 , 14, 414		15
34	Electrical Characterization of Ultra-Shallow Junctions Formed by Diffusion from a CoSi ₂ Diffusion Source. <i>Materials Research Society Symposia Proceedings</i> , 1996 , 427, 493		
33	Atomic force microscopy on SiO ₂ layers grown on Ge implanted silicon. <i>Nuclear Instruments & Methods in Physics Research B</i> , 1996 , 116, 482-485	1.2	2
32	Ge ion implantation in Si for the fabrication of Si/Ge _x Si _{1-x} heterojunction transistors. <i>Materials Chemistry and Physics</i> , 1996 , 46, 156-160	4.4	5
31	High temperature annealing effects on the electrical characteristics of C implanted Si. <i>Journal of Applied Physics</i> , 1996 , 79, 3464-3469	2.5	9

30	Characterization of C coimplanted Ge _x Si _{1-x} epitaxial layers formed by high dose Ge ion implantation in (100) Si. <i>Journal of Applied Physics</i> , 1996 , 79, 3456-3463	2.5	5
29	Improved thermal stability of cobalt silicide formed by ion beam assisted deposition on polysilicon. <i>Applied Surface Science</i> , 1995 , 91, 19-23	6.7	2
28	Secondary defect annihilation in ion beam processed Si _{1-x} Ge _x layers using titanium silicide. <i>Applied Physics Letters</i> , 1995 , 67, 2931-2933	3.4	3
27	Arsenic and boron diffusion in silicon from implanted cobalt silicide layers. <i>Semiconductor Science and Technology</i> , 1995 , 10, 1362-1367	1.8	8
26	Two-Dimensional Aluminum Diffusion in Silicon: Experimental Results and Simulations. <i>Journal of the Electrochemical Society</i> , 1995 , 142, 1585-1590	3.9	7
25	Titanium Silicidation and Secondary Defect Annihilation in Ion Beam Processed SiGe Layers. <i>Materials Research Society Symposia Proceedings</i> , 1995 , 402, 149		
24	Diffusion and outdiffusion of aluminium implanted into silicon. <i>Semiconductor Science and Technology</i> , 1993 , 8, 488-494	1.8	25
23	Stress-induced precipitation of dopants diffused into Si and TiSi ₂ and CoSi ₂ implanted layers. <i>Semiconductor Science and Technology</i> , 1993 , 8, 1196-1203	1.8	6
22	Structure and defect characterization of epitaxial CoSi ₂ on Si(001) formed using an amorphous Co ₇₅ W ₂₅ sputtered layer. <i>Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena</i> , 1993 , 11, 1807		7
21	Formation and characterization of epitaxial CoSi ₂ on Si(001). <i>Applied Surface Science</i> , 1993 , 73, 108-116	6.7	4
20	Formation and characterization of Si/CoSi ₂ /Si epitaxial heterostructures. <i>Applied Surface Science</i> , 1993 , 73, 135-140	6.7	3
19	Diffusion and precipitation of As from a CoSi ₂ diffusion source. <i>Applied Surface Science</i> , 1993 , 73, 175-186	6.7	5
18	Pulsed laser melting and resolidification of metal silicide layers. <i>International Journal of Thermophysics</i> , 1993 , 14, 383-396	2.1	5
17	Epitaxial CoSi ₂ formation on Si(001) from an amorphous Co ₇₅ W ₂₅ sputtered layer. <i>Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena</i> , 1992 , 10, 2284		10
16	Boron diffusion in Co ₇₄ Ti ₂₆ amorphous alloy. <i>Applied Physics Letters</i> , 1992 , 60, 701-703	3.4	6
15	Titanium silicide as a diffusion source for phosphorous: precipitation and activation. <i>Applied Surface Science</i> , 1991 , 53, 190-195	6.7	8
14	Rapid thermal processing reliability of titanium silicide implanted with arsenic, boron and phosphorus. <i>Applied Surface Science</i> , 1991 , 53, 377-382	6.7	6
13	Precipitation of arsenic diffused into silicon from a TiSi ₂ source. <i>Journal of Applied Physics</i> , 1991 , 69, 7262-7271	3.1	14

12	Arsenic redistribution and out-diffusion in TiSi ₂ -Si bilayered structures. <i>Semiconductor Science and Technology</i> , 1990 , 5, 831-835	1.8	2
11	Titanium silicide as a diffusion source for arsenic. <i>Journal of Applied Physics</i> , 1990 , 67, 7174-7176	2.5	6
10	An energy dispersion spectroscopy technique to measure titanium silicide lateral diffusion. <i>Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films</i> , 1989 , 7, 2609-2613	2.9	8
9	Dependence of PtSi Schottky diode electrical behaviour on the platinum film thickness and on the annealing process. <i>Thin Solid Films</i> , 1988 , 161, 13-20	2.2	7
8	Graphite Assisted P and Al Implanted 4H-SiC Laser Annealing. <i>Materials Science Forum</i> ,1062, 204-208	0.4	0
7	Large Area Growth of Cubic Silicon Carbide Using Close Space PVT by Application of Homoepitaxial Seeding. <i>Materials Science Forum</i> ,1062, 74-78	0.4	2
6	Impact of N Doping on 3C-SiC Defects. <i>Materials Science Forum</i> ,1062, 69-73	0.4	
5	Electrical Scanning Probe Microscopy Investigation of Schottky and Metal-Oxide Junctions on Hetero-Epitaxial 3C-SiC on Silicon. <i>Materials Science Forum</i> ,1062, 400-405	0.4	
4	Residual Stress Measurement by Raman on Surface-Micromachined Monocrystalline 3C-SiC on Silicon on insulator. <i>Materials Science Forum</i> ,1062, 320-324	0.4	
3	The Development of Monolithic Silicon Carbide Intracortical Neural Interfaces for Long-Term Human Implantation. <i>Materials Science Forum</i> ,1062, 195-203	0.4	
2	Automatic Image Analysis of Stackingfault. <i>Materials Science Forum</i> ,1062, 283-287	0.4	
1	Neutron Detection Study through Simulations with Fluka. <i>Materials Science Forum</i> ,1062, 509-513	0.4	